

ST 2SC1674

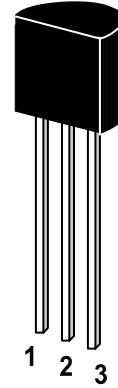
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NPN Silicon Epitaxial Planar Transistor

TV PIF amplifier, FM tuner RF amplifier.

The transistor is subdivided into three groups, R, O, and Y, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.

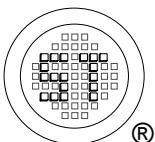


1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

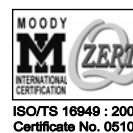
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	30	V
Collector Emitter Voltage	V_{CEO}	20	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103

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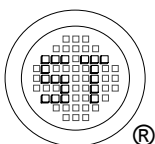
Dated : 07/12/2002

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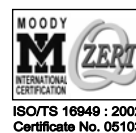
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$					
Current Gain Group R	h_{FE}	40	-	80	-
O	h_{FE}	70	-	140	-
Y	h_{FE}	120	-	240	-
Collector Base Breakdown Voltage at $I_C=10\mu\text{A}$	$V_{(BR)CBO}$	30	-	-	V
Collector Emitter Breakdown Voltage at $I_C=5\text{mA}$	$V_{(BR)CEO}$	20	-	-	V
Emitter Base Breakdown Voltage at $I_E=10\mu\text{A}$	$V_{(BR)EBO}$	4	-	-	V
Collector Cutoff Current at $V_{CB}=30\text{V}$	I_{CBO}	-	-	0.1	μA
Emitter Cutoff Current at $V_{EB}=4\text{V}$	I_{EBO}	-	-	0.1	μA
Collector Saturation Voltage at $I_C=10\text{mA}$, $I_B=1\text{mA}$	$V_{CE(sat)}$	-	0.1	0.3	V
Base Emitter On Voltage at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$	$V_{BE(on)}$	-	0.72	-	V
Gain Bandwidth Product at $V_{CE}=6\text{V}$, $I_C=1\text{mA}$	f_T	400	600	-	MHz
Output Capacitance at $V_{CB}=6\text{V}$, $f=1\text{MHz}$	C_{OB}	-	1.2	-	pF
Common Source Noise Figure at $V_{CE}=6\text{V}$, $f=100\text{MHz}$, $I_E=1\text{mA}$, $R_S=50\Omega$	NF	-	3	5	dB
Power Gain at $V_{CE}=6\text{V}$, $f=100\text{MHz}$, $I_E=1\text{mA}$, $R_S=50\Omega$	G_{pe}	18	22	-	dB



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